

Listing of claims:

1. (Currently amended) An etching solution for the production of integrated circuits comprising 5- 20% by weight hydrofluoric acid,
~~an organic~~ a solvent mixture consisting essentially of, ~~individually or as a mixture~~ at least two which are selected from ethylene glycol, propylene glycol, ethanol, ~~and or~~ glycerol,
and
1-20 % by weight water ~~for the production of integrated circuits.~~

2. (Canceled)

3.(Canceled)

4.(Currently amended) An etching solution according to Claim 1, comprising, as ~~organic~~ solvent mixture, ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

5.(Currently amended) An etching solution according to Claim 1, comprising, as ~~organic~~ solvent mixture, ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

6. (Canceled)

7. (Previously presented) An etching solution according to Claim 1, comprising a mixture of high-purity individual components.

8. (Withdrawn) A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 1.

9. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron doped glass.

10. (Withdrawn) A method according to claim 8, wherein said doped silicate is phosphorous doped glass.

11. (Withdrawn) A method according to claim 8, wherein said doped silicate is boron-phosphorous doped glass.

12. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a spin etcher.

13. (Withdrawn) A method according to claim 8, wherein said selective etching is carried out in a drip etcher.

14. (Previously presented) An etching solution according to claim 1, wherein said water is from 6.4 -20 % by weight.

15. (New) An etching solution comprising:

5- 20% by weight hydrofluoric acid,

a solvent mixture consisting essentially of at least two solvents selected from ethylene glycol,

propylene glycol, ethanol, or glycerol,

and

1-20 % by weight water for the etching of doped silicate layers.

16. (New) An etching solution comprising:

5- 20% by weight hydrofluoric acid,

a solvent mixture comprising at least two solvents selected from ethylene glycol, propylene

glycol, ethanol, or glycerol,

and

1-20 % by weight water for the etching of doped silicate layers.